

## **BUK751R8-40E**

# N-channel TrenchMOS standard level FET 11 September 2012

**Product data sheet** 

#### **Product profile** 1.

#### 1.1 General description

Standard level N-channel MOSFET in a SOT78 package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

#### 1.2 Features and benefits

- AEC Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with VGS(th) rating of greater than 1V at 175 °C

### 1.3 Applications

- 12 V Automotive systems
- Electric and electro-hydraulic power steering
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

#### 1.4 Quick reference data

Quick reference data Table 1.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	40	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>	[1]	-	-	120	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	-	349	W
Static characte	Static characteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ Fig. 11		_	1.5	1.8	mΩ
Dynamic characteristics							
$Q_{GD}$	gate-drain charge	$V_{GS}$ = 10 V; $I_D$ = 25 A; $V_{DS}$ = 32 V; Fig. 13; Fig. 14		-	48.2	-	nC

<sup>[1]</sup> Continuous current is limited by package.



### 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D I
2	D	drain	$1 \qquad 7 \qquad 7$	
3	S	source		G C
mb	D	mounting base; connected to drain		mbb076 S
			TO-220AB (SOT78A)	

### 3. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BUK751R8-40E	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78A			

### 4. Marking

Table 4. Marking codes

Type number	Marking code
BUK751R8-40E	BUK751R8-40E

### 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	40	V
$V_{DGR}$	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$		-	40	V
$V_{GS}$	gate-source voltage	T <sub>j</sub> ≤ 175 °C; DC		-20	20	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u>	[1]	-	120	Α
		T <sub>mb</sub> = 100 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u>	[1]	-	120	Α
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; pulsed; $t_p \le 10 \mu s$ ; Fig. 4		-	1278	Α

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Symbol	Parameter	Conditions		Min	Max	Unit
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	349	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drai	n diode				'	
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	120	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	1278	Α
Avalanche ruggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D$ = 120 A; $V_{sup} \le 40$ V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 3	[2][3]	-	1020	mJ

- [1] Continuous current is limited by package.
- [2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [3] Refer to application note AN10273 for further information.

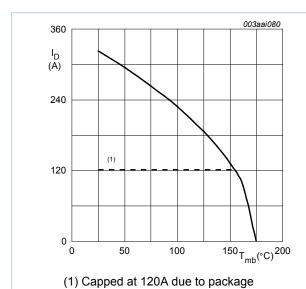


Fig. 1. Continuous drain current as a function of mounting base temperature

 $V_{GS} \ge 10V$ 

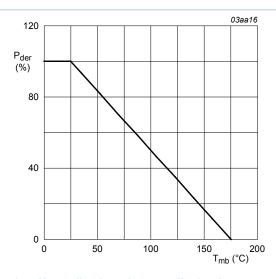


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \,\%$$

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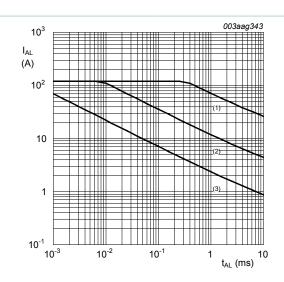
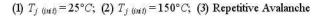


Fig. 3. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time



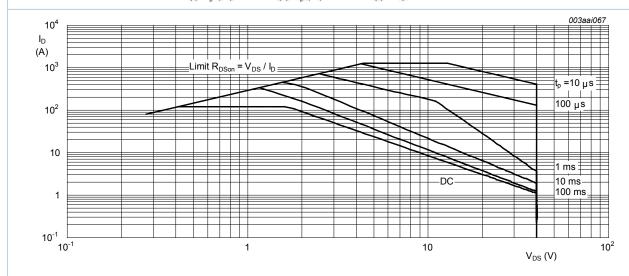


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

 $T_{mb} = 25^{\circ}C$ ;  $I_{DM}$  is a single pulse

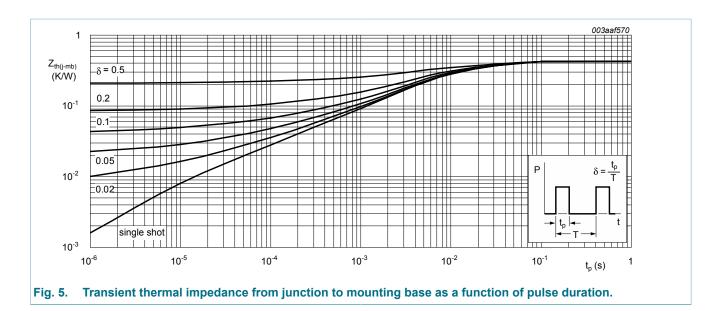
#### 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 5	_	_	0.43	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	vertical in still air	-	60	-	K/W

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### 7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
$V_{(BR)DSS}$	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	40	-	-	V
breal	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	36	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 9; Fig. 10	2.4	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10	-	-	4.5	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 10	1	-	-	V
I <sub>DSS</sub> drain leakage current	V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.25	3	μA	
		V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-	500	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>	-	1.5	1.8	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; Fig. 12; Fig. 11	-	-	3.4	mΩ
Dynamic ch	naracteristics			'		_
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 32 V; V <sub>GS</sub> = 10 V;	-	145	-	nC
$Q_{GS}$	gate-source charge	Fig. 13; Fig. 14	-	35.7	-	nC
$Q_{GD}$	gate-drain charge		-	48.2	-	nC

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C <sub>iss</sub>	input capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz;	-	8500	11340	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 15</u>	-	1620	1950	pF
C <sub>rss</sub>	reverse transfer capacitance		-	985	1350	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 10 \text{ V};$	-	42	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega$	-	60	-	ns
$t_{d(off)}$	turn-off delay time		-	121	-	ns
t <sub>f</sub>	fall time		-	83	-	ns
L <sub>D</sub> internal drain inductance		from drain lead 6mm from package to centre of die	-	4.5	-	nH
		from upper edge of drain mounting base to center of die	-	2.5	-	nH
L <sub>S</sub>	internal source inductance	from source lead to source bonding pad	-	7.5	-	nH
Source-dra	in diode		1	'		,
$V_{SD}$	source-drain voltage	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; <u>Fig. 16</u>	-	0.77	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	56	-	ns
Qr	recovered charge	V <sub>DS</sub> = 25 V	-	94	-	nC

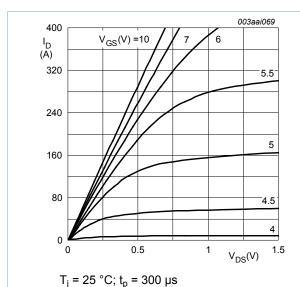


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

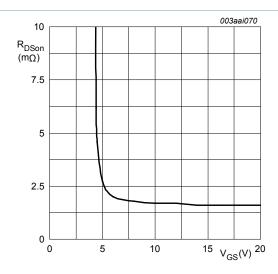


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25^{\circ}C; I_D = 25A$$

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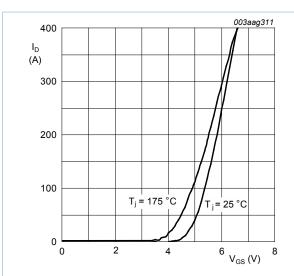


Fig. 8. Transfer characteristics: drain current as a function of gate-source voltage; typical values



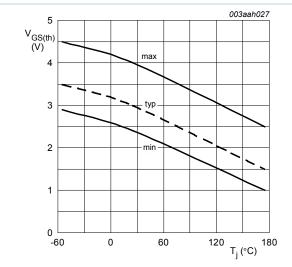


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 \text{ mA}; \ V_{DS} = V_{GS}$$

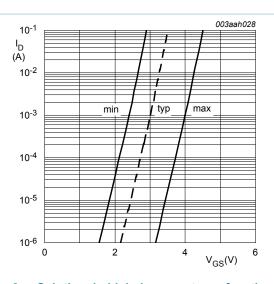
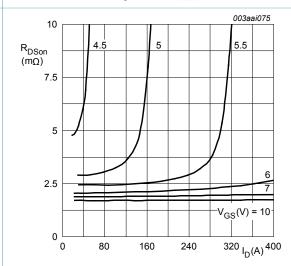


Fig. 9. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25^{\circ}C; \ V_{DS} = 5V$$



 $T_i = 25 \,^{\circ}\text{C}; t_p = 300 \,\mu\text{s}$ 

Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

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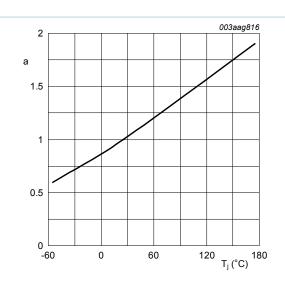


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$\mathbf{a} = \frac{R_{DSon}}{R_{DSon(25~\%)}}$$

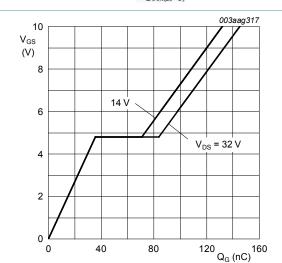


Fig. 14. Gate-source voltage as a function of gate charge; typical values

 $T_i = 25 \,^{\circ}C; I_D = 25 \,^{\circ}A$ 

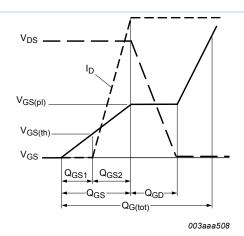


Fig. 13. Gate charge waveform definitions

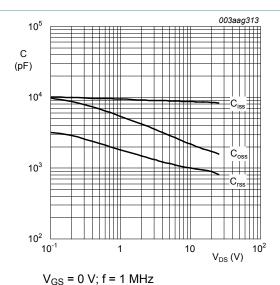
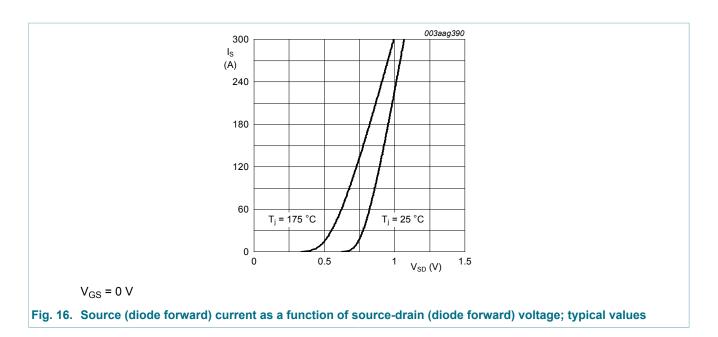


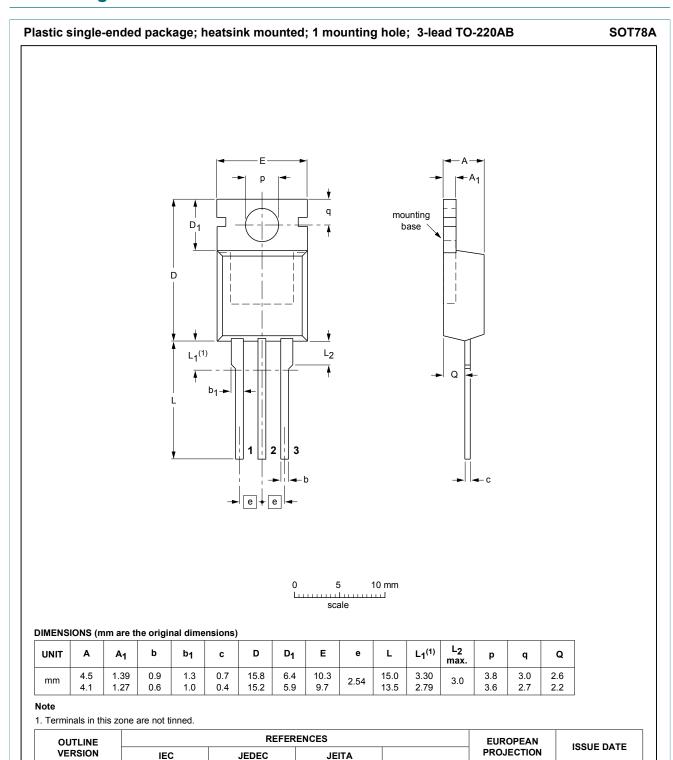
Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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### 8. Package outline



#### Fig. 17. Package outline TO-220AB (SOT78A)

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3-lead TO-220AB

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SOT78A

SC-46

### 9. Legal information

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